

What is claimed is:

1. A semiconductor die, comprising:  
an integrated circuit supported by a substrate and having a plurality of integrated circuit devices, wherein at least one of the plurality of integrated circuit devices comprises a capacitor, the capacitor comprising:
  - a bottom electrode;
  - a first metal oxynitride barrier layer overlying the bottom electrode;
  - a metal oxide dielectric layer overlying the first metal oxynitride barrier layer;
  - a second metal oxynitride barrier layer overlying the metal oxide dielectric layer; and
  - a top electrode overlying the second metal oxynitride barrier layer.
2. The semiconductor die of claim 1, wherein each metal oxynitride barrier layer individually comprises a metal oxynitride having a composition of the form  $\text{MO}_x\text{N}_y$ , wherein M is a metal component selected from the group consisting of chromium, cobalt, hafnium, iridium, molybdenum, niobium, osmium, rhenium, rhodium, ruthenium, tantalum, titanium, tungsten, vanadium and zirconium.
3. The semiconductor die of claim 2, wherein the metal component of the first metal oxynitride barrier layer is the same as the metal component of the second metal oxynitride barrier layer.
4. The semiconductor die of claim 2, wherein x ranges from approximately 0.05 to approximately one-half the maximum valence value of the metal component M minus 0.05 and y ranges from approximately 0.1 to approximately the maximum valence value of the metal component M minus 0.1.

5. The semiconductor die of claim 2, wherein M is a metal component selected from the group consisting of chromium, hafnium, molybdenum and tungsten, and wherein x ranges from approximately 0.05 to approximately 2.95 and y ranges from approximately 0.1 to approximately 5.9.
6. The semiconductor die of claim 1, wherein each metal oxynitride barrier layer individually comprises a tungsten oxynitride having a composition of the form  $WO_xNy$ , wherein x ranges from approximately 0.05 to approximately 2.95 and y ranges from approximately 0.1 to approximately 5.9.
7. The semiconductor die of claim 1, wherein at least one electrode comprises a metal nitride.
8. The semiconductor die of claim 1, wherein at least one electrode comprises tungsten nitride.
9. The semiconductor die of claim 1, wherein the bottom electrode comprises a metal nitride having a metal component the same as the metal component of the first metal oxynitride barrier layer.
10. A semiconductor die, comprising:
  - an integrated circuit supported by a substrate and having a plurality of integrated circuit devices, wherein at least one of the plurality of integrated circuit devices comprises a capacitor, the capacitor comprising:
    - a bottom metal nitride electrode;
    - a first metal oxynitride barrier layer overlying the bottom metal nitride electrode;
    - a metal oxide dielectric layer overlying the first metal oxynitride barrier

layer;

a second metal oxynitride barrier layer overlying the dielectric layer; and  
a top metal nitride electrode overlying the second metal oxynitride  
barrier layer.

11. The semiconductor die of claim 10, wherein the metal oxide layer comprises tantalum oxide.

12. The semiconductor die of claim 10, wherein the bottom and top electrodes comprise tungsten nitride.

13. A semiconductor die, comprising:

an integrated circuit supported by a substrate and having a plurality of integrated circuit devices, wherein at least one of the plurality of integrated circuit devices comprises a capacitor, the capacitor comprising:

a bottom electrode having a bottom electrode metal component;  
a top electrode having a top electrode metal component;  
a dielectric layer interposed between the bottom electrode and the top  
electrode;

an oxynitride barrier layer having a barrier metal component, wherein the barrier metal component is different from the bottom electrode metal component or wherein the barrier metal component is different from the top electrode metal component, wherein the oxynitride barrier layer is interposed between the dielectric layer and the bottom electrode or wherein the metal oxynitride barrier layer is interposed between the dielectric layer and the top electrode; and

a second barrier layer, wherein the second barrier layer is interposed between the dielectric layer and the bottom electrode or wherein the second layer is interposed between the dielectric layer and the top electrode.

14. The semiconductor die of claim 13, wherein the metal oxynitride barrier layer comprises  $\text{MO}_x\text{N}_y$ , wherein M is a metal selected from the group consisting of: chromium, cobalt, hafnium, iridium, molybdenum, niobium, osmium, rhenium, rhodium, ruthenium, tantalum, titanium, tungsten, vanadium and zirconium.
15. The semiconductor die of claim 14, wherein x ranges from approximately 0.05 to approximately one-half the maximum valence value of the metal M minus 0.05 and y ranges from approximately 0.1 to approximately the maximum valence value of the metal M minus 0.1.
16. The semiconductor die of claim 14, wherein M is a metal selected from the group consisting of chromium, hafnium, molybdenum and tungsten, and wherein x ranges from approximately 0.05 to approximately 2.95 and y ranges from approximately 0.1 to approximately 5.9.
17. The semiconductor die of claim 13, wherein the metal oxynitride barrier layer comprises a tungsten oxynitride having a composition of the form  $\text{WO}_x\text{N}_y$ , wherein x ranges from approximately 0.05 to approximately 2.95 and y ranges from approximately 0.1 to approximately 5.9.
18. The semiconductor die of claim 13, wherein at least one of the top and bottom electrodes comprises a metal nitride.
19. The semiconductor die of claim 13, wherein at least one of the top and bottom electrodes comprises tungsten nitride.
20. The semiconductor die of claim 13, wherein the dielectric layer comprises a metal oxide dielectric material selected from the group consisting of  $\text{Ba}_z\text{Sr}(1-z)\text{TiO}_3$ ,

(where  $0 < z < 1$ ), BaTiO<sub>3</sub>, SrTiO<sub>3</sub>, PbTiO<sub>3</sub>, Pb(Zr,Ti)O<sub>3</sub>, (Pb,La)(Zr,Ti)O<sub>3</sub>, (Pb,La)TiO<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub>, KNO<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub> and LiNbO<sub>3</sub>.

21. The semiconductor die of claim 13, wherein the dielectric layer comprises tantalum oxide.

22. A semiconductor die, comprising:

an integrated circuit supported by a substrate and having a plurality of integrated circuit devices, wherein at least one of the plurality of integrated circuit devices comprises a capacitor, the capacitor comprising:

a bottom electrode having a bottom electrode metal component;  
a top electrode having a top electrode metal component;  
a dielectric layer interposed between the bottom electrode and the top electrode;

a tungsten oxynitride barrier layer having a barrier metal component, wherein the barrier metal component is different from the bottom electrode metal component or wherein the barrier metal component is different from the top electrode metal component, wherein the tungsten oxynitride barrier layer is interposed between the dielectric layer and the bottom electrode or wherein the tungsten oxynitride barrier layer is interposed between the dielectric layer and the top electrode; and

a second barrier layer, wherein the second barrier layer is interposed between the dielectric layer and the bottom electrode or wherein the second layer is interposed between the dielectric layer and the top electrode.

23. The semiconductor die of claim 22, wherein the tungsten oxynitride barrier layer has a composition of the form WO<sub>x</sub>N<sub>y</sub>, wherein x ranges from approximately 0.05 to approximately 2.95 and y ranges from approximately 0.1 to approximately 5.9.

24. The semiconductor die of claim 22, wherein at least one of the top and bottom electrodes comprises a metal nitride.